



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: ASADA, Hitoshi et al.

Group Art Unit: 2811

Serial No.: 09/753,616

Examiner: Gebremariam, Samuel

Filed: January 4, 2001

P.T.O. Confirmation No.: 1580

For. CMOS IMAGE SENSOR AND MANUFACTURING METHOD OF THE SAME

PRELIMINARY AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

Date: March 7, 2003

Sir:

Prior to continued examination on the merits, please amend the above-captioned patent application as follows:

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IN THE CLAIMS:

Please amend claim 2 as follows:

2. (Twice Amended) A CMOS image sensor comprising a pixel consisting of:
- a photodiode having an impurity region formed in semiconductor substrate;
  - a first MOS transistor formed on said semiconductor substrate, the first MOS transistor having an impurity region as a drain connected to said impurity region of said photodiode;
  - a second MOS transistor formed on said semiconductor substrate, the second MOS transistor having an impurity region as a source connected to a source of said first MOS transistor; and
  - a third MOS transistor formed on said semiconductor substrate, the third MOS transistor having an impurity region as a source connected to a drain of said second MOS transistor,

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